

KBP2005-KBP210/G

Single Phase 2.0Amp Glass passivated Bridge Rectifiers

Features

Mechanical Data

- Rating to 1000V PRV
- · Idea for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- The plastic material has UL flammability classification
 94V-0
- The G suffix is uses for photoresist chip, otherwise it is a knife scraping chip

MECHANICAL DATA

- Polarity : As marked on body
- Weight : 0.05 ounces, 1.52 grams
- Mounting position : Any

Maximum Ratings And Electrical Characteristics (@T_A=25°C unless otherwise noted)

Symbol	Parameter	KBP	KBP	KBP	KBP	KBP	KBP	KBP	Unit
		2005	201	202	204	206	208	210	
V _{RRM}	Maximum repetitive peak reverse voltage	50	100	200	400	600	800	1000	V
V _{RMS}	Maximum RMS voltage	35	70	140	280	420	560	700	V
V _{DC}	Maximum DC blocking voltage	50	100	200	400	600	800	1000	V
I _{AV}	Maximum average forward	20						A	
	rectified current @T _C =100 $^{\circ}$ C	2.0							
I _{FSM}	Peak forward surge current, 8.3ms single	60						Δ	
	half sine-wave @ T_J =25 $^{\circ}$ C								
V_{F}	Maximum forward voltage at 2.0A DC	1.10					V		
	Maximum DC reverse current @ T_J =25°C	5.0					uA		
IR	at rated DC blocking voltage @T _J =125 $^{\circ}$ C	500							
I_t^2	I ² Rating for fusing (3ms≤t≤8.3ms)	14.94			A _S ²				
CJ	Typical junction capacitance (Note 1)	25				pF			
R _{θJC}		10 18							
$R_{ ext{ heta}JL}$	Typical thermal resistance(Note 2)						°C/W		
R _{0JA}	40					1			
TJ	Operation Temperature Range	-55 to +150				° c			
T _{STG}	Storage Temperature Range	-55 to +150							

Note:(1)Measured at 1MHz and applied reverse voltage of 4.0V D.C.

(2)Thermal Resistance Junction to Case, Lead and Ambient.

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Ratings And Characteristic Curves

Figure 1: FORWARD CURRENT DERATING CURVE





Figure 3: TYPICAL JUNCTION CAPACITANCE



Figure 5:TYPICAL REVERSE CHARACTERISTICS



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Figure 4: TYPICAL FORWARD CHARACTERISTICS









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Outline Drawing -KBP



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	MILLIMETER				
STMBUL	MIN.	MAX.			
А	14.2	14.7			
В	3.30	3.60			
С	10.2	10.6			
D	13.8	14.4			
d	1.40	1.70			
Е	1.80	2.20			
F	0.80	1.10			
G	3.71	3.91			
Н	0.30	0.55			
I	1.22	1.42			
J	0.76	0.86			
К	2.7 x 45°				
L	-	3 °			
М	-	2 °			

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Specifications are subject to change without notice. Please refer to http://www.born-tw.com for current information. Revision: 2022-Jan-1

